

Features

- Excellent dynamic characteristics
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Design for inverter supply application

品名 : FH1200TN

 $I_{T(AV)}$ 1200A V_{DRM} 2000V~3000V V_{RRM} 1000V~2500V t_q 20~75μs

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	$T_C=55^{\circ}\text{C}$	125		1200	A
			$T_C=70^{\circ}\text{C}$	125		1000	A
V_{DRM}	Repetitive peak off-state voltage	tp=10ms	125	2000		3000	V
V_{RRM}	Repetitive peak reverse voltage			1000		2500	
I_{DRM}/I_{RRM}	Repetitive peak current	at V_{DRM}/V_{RRM}	125			80	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			16	kA
I^2t	I^2t for fusing coordination					1280	$10^3\text{A}^2\text{s}$
V_{TO}	Threshold voltage		125			1.55	V
r_T	On-state slope resistance					0.40	$\text{m}\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=3000\text{A}, F=24\text{kN}$	$20 \leq t_q \leq 35$	25		2.80	V
			$36 \leq t_q \leq 60$			2.60	V
			$61 \leq t_q \leq 75$			2.40	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of on-state current (Non-repetitive)	$V_{DM}=67\%V_{DRM}$ to 1600A, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$	125			1500	$\text{A}/\mu\text{s}$
Q_{rr}	Recovery charge	$I_{TM}=1000\text{A}$, tp=4000μs, $di/dt=-20\text{A}/\mu\text{s}$, $V_R=100\text{V}$	125		750		μC
t_q	Circuit commutated turn-off time	$I_{TM}=1000\text{A}$, tp=4000μs, $V_R=100\text{V}$ $dv/dt=30\text{V}/\mu\text{s}$, $di/dt=-20\text{A}/\mu\text{s}$	100	20		75	μs
I_{GT}	Gate trigger current	$V_A=12\text{V}, I_A=1\text{A}$	25	40		300	mA
V_{GT}	Gate trigger voltage			0.9		3.0	V
I_H	Holding current			20		500	mA
I_L	Latching current					500	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	DC double side cooled Clamping force 24kN				0.020	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.005	
F_m	Mounting force			19		26	kN
T_{vj}	Junction temperature			-40		125	$^{\circ}\text{C}$
T_{stg}	Stored temperature			-40		140	$^{\circ}\text{C}$
W_t	Weight				440		g
Outline		P11					

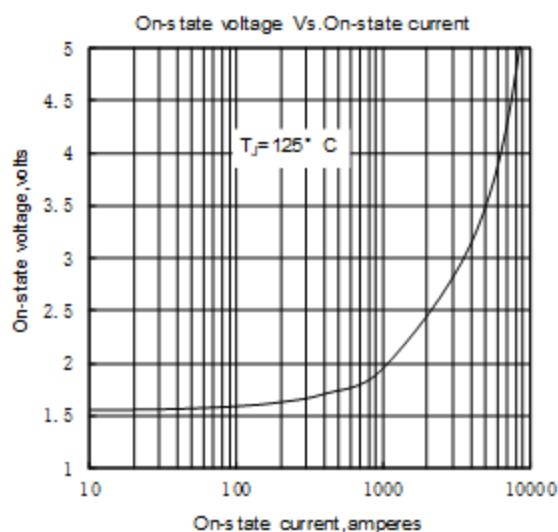


Fig. 1

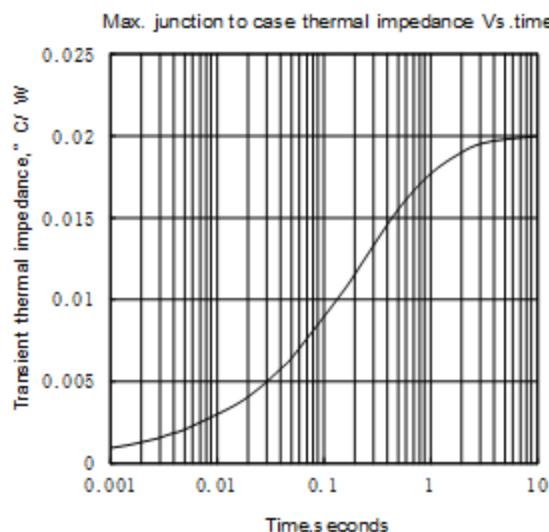


Fig. 2

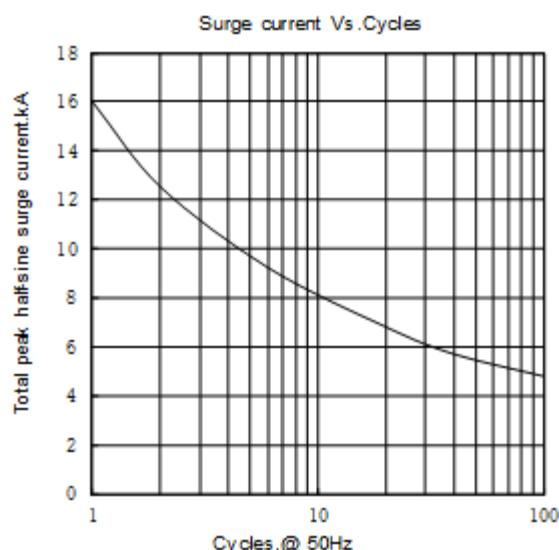


Fig. 3

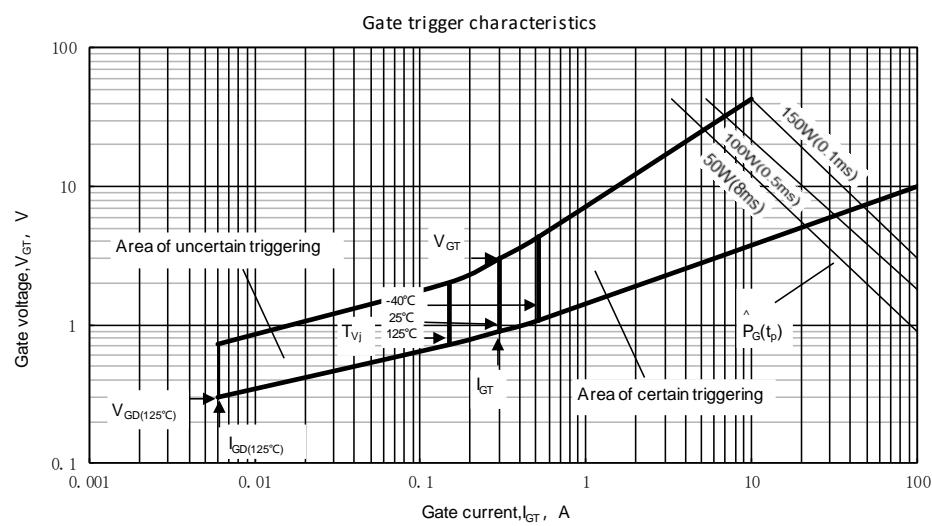
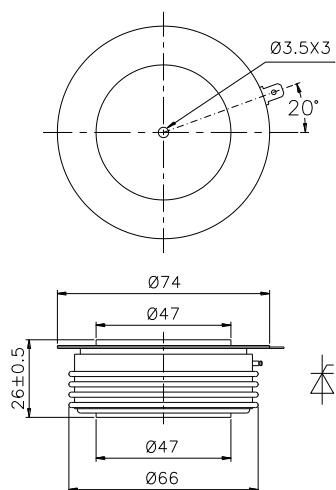


Fig. 4



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